



YJT280G10HJ

RECOMMEND
YJT300G10H
FOR NEW DESIGN

N-Channel Enhancement Mode Field Effect Transistor

Product Summary



YJT280G10HJ

RECOMMEND
[YJT300G10H](#)
FOR NEW DESIGN

Typical Electrical and Thermal Characteristics Diagrams

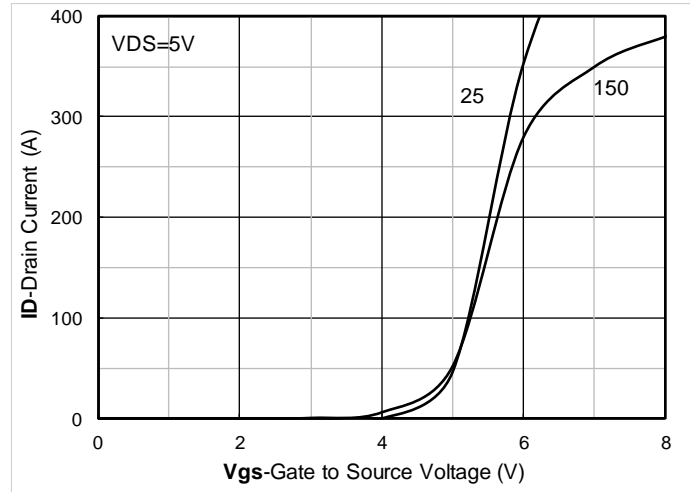


Figure 2. Transfer Characteristics

Figure 1. Output Characteristics

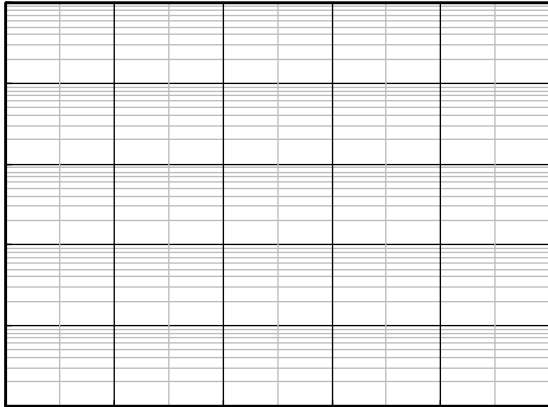


Figure 3. Capacitance Characteristics

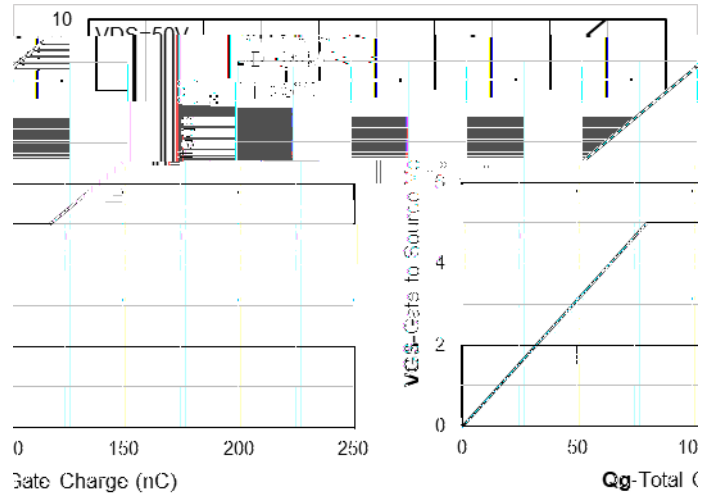


Figure 4. Gate Charge

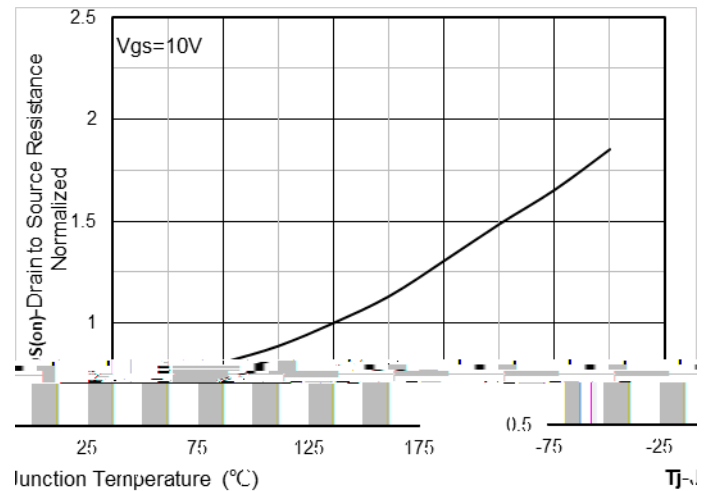
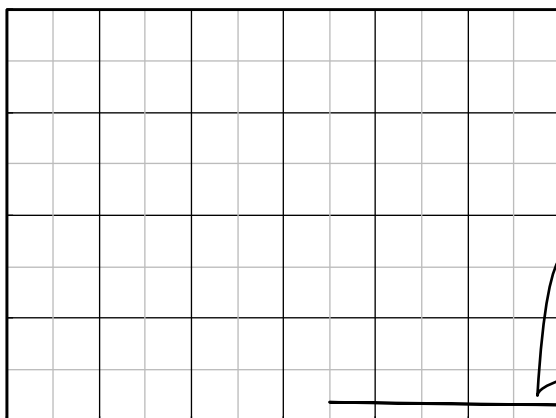


Figure 5. On-Resistance vs Gate to Source Voltage

RECOMMEND
YJT300G10H
FOR NEW DESIGN

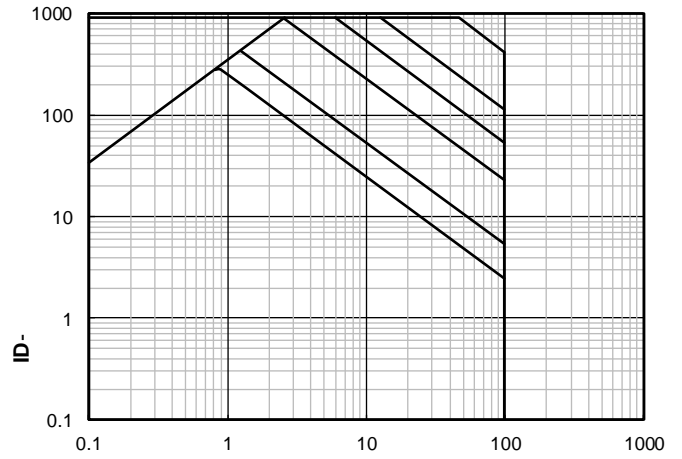


Figure 13. Maximum Transient Thermal Impedance

Figure 14. Safe Operation Area

Test Circuits & Waveforms

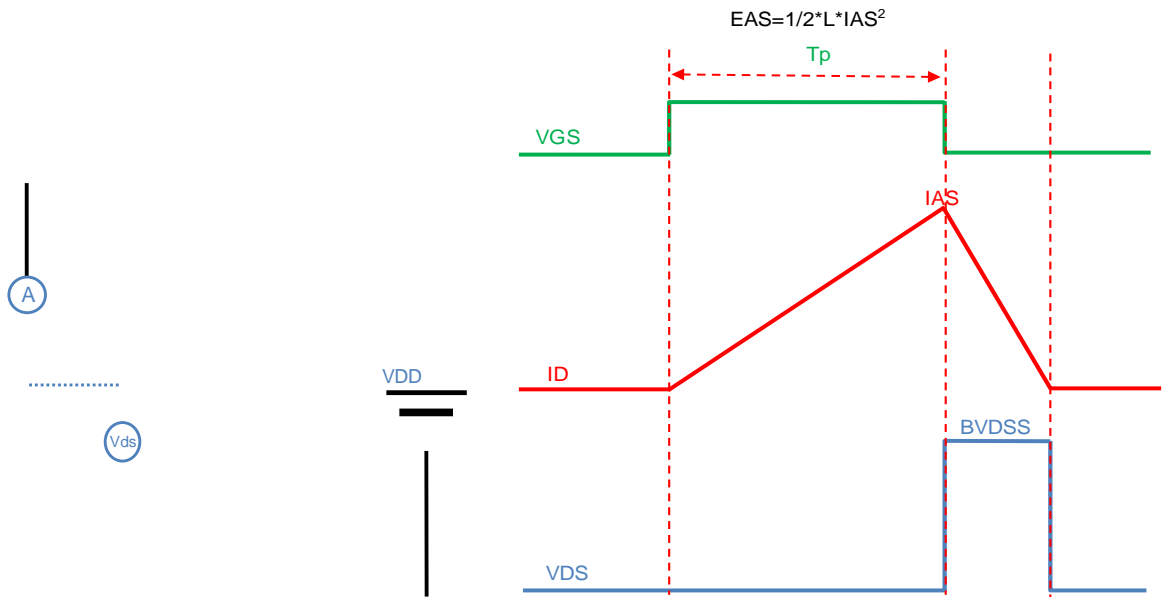


Figure A.



YJT280G10HJ

RECOMMEND
[YJT300G10H](#)
FOR NEW DESIGN

TOLL Package information
TYPE A



Disclaimer

The information presented in this document is for reference only. Yangzhou Yangjie Electronic Technology Co., Ltd. reserves the right to make changes without notice for the specification of the products displayed herein to improve reliability, function or design or otherwise.

The product listed herein is designed to be used with ordinary electronic equipment or devices, and not designed to be used with equipment or devices which require high level of reliability and the malfunction of which would directly endanger human life (such as medical instruments, transportation equipment, aerospace machinery, nuclear-reactor controllers, fuel controllers and other safety devices), Yangjie or anyone on its behalf, assumes no responsibility or liability for any damages resulting from such improper use of sale.

This publication supersedes & replaces all information previously supplied. For additional information, please visit our website <http://www.21yangjie.com>

NOT RECOMMENDED
FOR NEW DESIGN